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**Amendments to the Claims**

Claims 1-60 (Cancelled).

61. (New) A semiconductor construction comprising:

a first conductive pillar having a lower portion disposed between a first pair of wordlines and an upper portion extending at least partially over each of the first pair of wordlines;

a first conductive stem in contact with the first conductive pillar, the first conductive stem being formed by a process comprising:

forming an insulative layer over the conductive pillar;

forming a conductive material over the insulative material;

forming a masking material over the conductive material;

utilizing photolithography, patterning an opening through the masking material, the opening having a feature width defined by the photolithography;

narrowing the opening to a narrowed opening;

extending the narrowed opening through the conductive material and through the insulative material; and

depositing a stem material within the extended opening to produce the stem having width that is less than the feature width;

a first pair of laterally opposed fins extending laterally from the first conductive stem;

a second conductive pillar having a lower portion disposed between a second pair of wordlines and an upper portion extending at least partially over each of the second pair of wordlines;

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a second conductive stem comprising the stem width, in contact with the second conductive pillar; and

a second pair of laterally opposed fins extending laterally from the second stem.

62. (New) The semiconductor construction of claim 61 wherein a distance between a first fin comprised by the first pair of opposed fins and a second fin comprised by the second pair of opposed fins is less than the feature width.

63. (New) The semiconductor construction of claim 61 wherein the first and second conductive stems comprise polysilicon.

64. (New) The semiconductor construction of claim 61 wherein the first and second pair of opposed fins comprise polysilicon.

65. (New) The semiconductor construction of claim 61 wherein the first and second pair of opposed fins are coated with a layer of dielectric material.

66. (New) The semiconductor construction of claim 61 wherein the first conductive pillar, the first conductive stem, and the first pair of laterally opposed fins are comprised by a first capacitor construction which further comprises a third pair of laterally opposed fins extending laterally from the first conductive stem.

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67. (New) This semiconductor construction of claim 66 wherein the first conductive pillar, the first conductive stem, and the first and third pairs of laterally opposed fins each comprise polysilicon.